

# BCP53T1 Series

Preferred Devices

## PNP Silicon Epitaxial Transistors

This PNP Silicon Epitaxial transistor is designed for use in audio amplifier applications. The device is housed in the SOT-223 package which is designed for medium power surface mount applications.

- High Current: 1.5 Amps
- NPN Complement is BCP56
- The SOT-223 Package can be soldered using wave or reflow. The formed leads absorb thermal stress during soldering, eliminating the possibility of damage to the die
- Available in 12 mm Tape and Reel
  - Use BCP53T1 to order the 7 inch/1000 unit reel.
  - Use BCP53T3 to order the 13 inch/4000 unit reel.
- Device Marking:
  - BCP53T1 = AH
  - BCP53-10T1 = AH-10
  - BCP53-16T1 = AH-16

### MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)

| Rating  | Symbol                            | Value          | Unit           |
|---|-----------------------------------|----------------|----------------|
| Collector-Emitter Voltage   | V <sub>CEO</sub>                  | -80            | Vdc            |
| Collector-Base Voltage  | V <sub>CBO</sub>                  | -100           | Vdc            |
| Emitter-Base Voltage  | V <sub>EBO</sub>                  | -5.0           | Vdc            |
| Collector Current   | I <sub>C</sub>                    | 1.5            | Adc            |
| Total Power Dissipation<br>@ T <sub>A</sub> = 25°C (Note 1.)<br>Derate above 25°C | P <sub>D</sub>                    | 1.5<br>12      | Watts<br>mW/°C |
| Operating and Storage<br>Temperature Range  | T <sub>J</sub> , T <sub>stg</sub> | -65 to<br>+150 | °C             |

### THERMAL CHARACTERISTICS

| Characteristic  | Symbol           | Max       | Unit      |
|---|------------------|-----------|-----------|
| Thermal Resistance,<br>Junction to Ambient<br>(surface mounted)             | R <sub>θJA</sub> | 83.3      | °C/W      |
| Lead Temperature for Soldering,<br>0.0625" from case<br>Time in Solder Bath | T <sub>L</sub>   | 260<br>10 | °C<br>Sec |

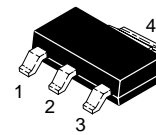
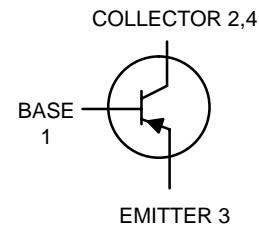
1. Device mounted on a glass epoxy printed circuit board 1.575 in. x 1.575 in. x 0.059 in.; mounting pad for the collector lead min. 0.93 sq. in.



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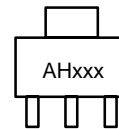
<http://onsemi.com>

## MEDIUM POWER HIGH CURRENT SURFACE MOUNT PNP TRANSISTORS



SOT-223  
CASE 318E  
STYLE 1

### MARKING DIAGRAM



AHxxx = Device Code  
xxx = -10 or -16

### ORDERING INFORMATION

| Device     | Package | Shipping         |
|------------|---------|------------------|
| BCP53T1    | SOT-223 | 1000/Tape & Reel |
| BCP53T3    | SOT-223 | 4000/Tape & Reel |
| BCP53-10T1 | SOT-223 | 1000/Tape & Reel |
| BCP53-10T3 | SOT-223 | 4000/Tape & Reel |
| BCP53-16T1 | SOT-223 | 1000/Tape & Reel |
| BCP53-16T3 | SOT-223 | 4000/Tape & Reel |

Preferred devices are recommended choices for future use and best overall value.

# BCP53T1 Series

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristics  | Symbol        | Min                         | Typ                   | Max                         | Unit            |
|--|---------------|-----------------------------|-----------------------|-----------------------------|-----------------|
| <b>OFF CHARACTERISTICS</b>   |               |                             |                       |                             |                 |
| Collector-Base Breakdown Voltage ( $I_C = -100 \mu\text{Adc}$ , $I_E = 0$ )  | $V_{(BR)CBO}$ | -100                        | -                     | -                           | Vdc             |
| Collector-Emitter Breakdown Voltage ( $I_C = -1.0 \text{ mAdc}$ , $I_B = 0$ )  | $V_{(BR)CEO}$ | -80                         | -                     | -                           | Vdc             |
| Collector-Emitter Breakdown Voltage ( $I_C = -100 \mu\text{Adc}$ , $R_{BE} = 1.0 \text{ kohm}$ )   | $V_{(BR)CER}$ | -100                        | -                     | -                           | Vdc             |
| Emitter-Base Breakdown Voltage ( $I_E = -10 \mu\text{Adc}$ , $I_C = 0$ )   | $V_{(BR)EBO}$ | -5.0                        | -                     | -                           | Vdc             |
| Collector-Base Cutoff Current ( $V_{CB} = -30 \text{ Vdc}$ , $I_E = 0$ )   | $I_{CBO}$     | -                           | -                     | -100                        | nAdc            |
| Emitter-Base Cutoff Current ( $V_{EB} = -5.0 \text{ Vdc}$ , $I_C = 0$ )  | $I_{EBO}$     | -                           | -                     | -10                         | $\mu\text{Adc}$ |
| <b>ON CHARACTERISTICS</b>  |               |                             |                       |                             |                 |
| DC Current Gain ( $I_C = -5.0 \text{ mAdc}$ , $V_{CE} = -2.0 \text{ Vdc}$ ) All Part Types<br>( $I_C = -150 \text{ mAdc}$ , $V_{CE} = -2.0 \text{ Vdc}$ )<br>BCP53T1<br>BCP53-10T1<br>BCP53-16T1<br><br>( $I_C = -500 \text{ mAdc}$ , $V_{CE} = -2.0 \text{ Vdc}$ ) All Part Types | $h_{FE}$      | 25<br>40<br>63<br>100<br>25 | -<br>-<br>-<br>-<br>- | -<br>250<br>160<br>250<br>- | -               |
| Collector-Emitter Saturation Voltage ( $I_C = -500 \text{ mAdc}$ , $I_B = -50 \text{ mAdc}$ )  | $V_{CE(sat)}$ | -                           | -                     | -0.5                        | Vdc             |
| Base-Emitter On Voltage ( $I_C = -500 \text{ mAdc}$ , $V_{CE} = -2.0 \text{ Vdc}$ )  | $V_{BE(on)}$  | -                           | -                     | -1.0                        | Vdc             |
| <b>DYNAMIC CHARACTERISTICS</b>   |               |                             |                       |                             |                 |
| Current-Gain – Bandwidth Product<br>( $I_C = -10 \text{ mAdc}$ , $V_{CE} = -5.0 \text{ Vdc}$ , $f = 35 \text{ MHz}$ )  | $f_T$         | -                           | 50                    | -                           | MHz             |

## TYPICAL ELECTRICAL CHARACTERISTICS

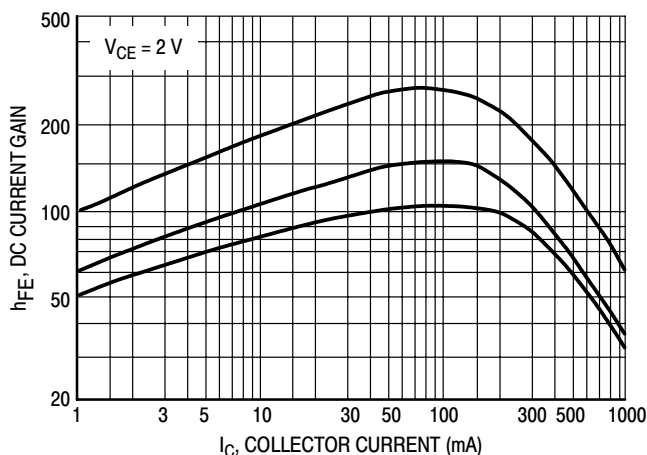


Figure 1. DC Current Gain

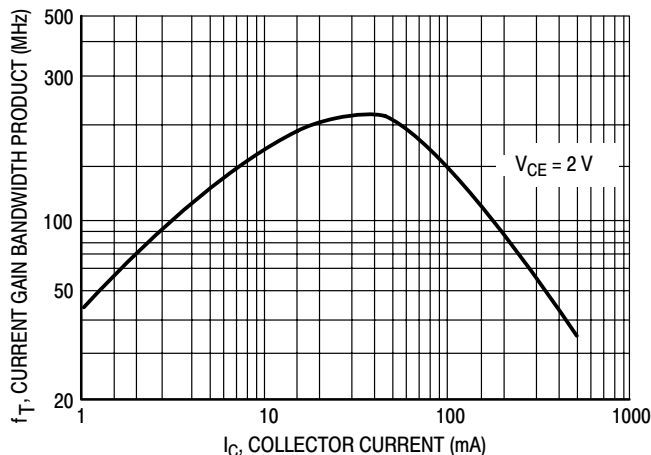


Figure 2. Current Gain Bandwidth Product

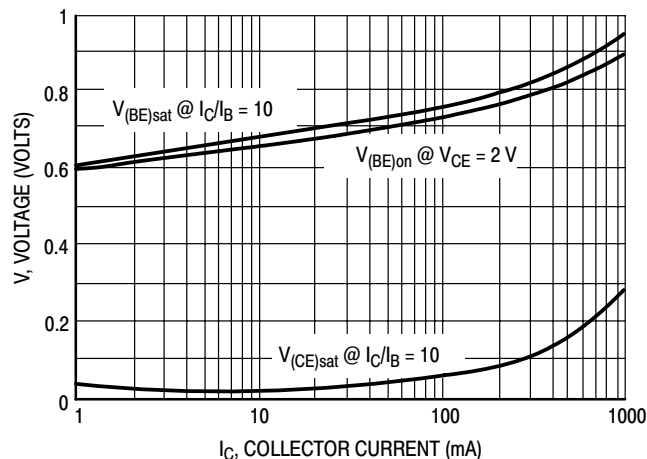


Figure 3. Saturation and "ON" Voltages

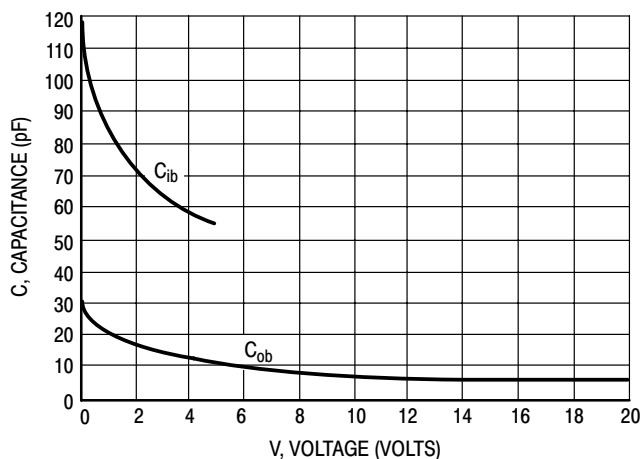


Figure 4. Capacitances

INFORMATION FOR USING THE SOT-223 SURFACE MOUNT PACKAGE

POWER DISSIPATION

The power dissipation of the SOT-223 is a function of the input pad size. These can vary from the minimum pad size for soldering to the pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by  $T_{J(max)}$ , the maximum rated junction temperature of the die,  $R_{\theta JA}$ , the thermal resistance from the device junction to ambient; and the operating temperature,  $T_A$ . Using the values provided on the data sheet for the SOT-223 package,  $P_D$  can be calculated as follows.

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values

into the equation for an ambient temperature  $T_A$  of 25°C, one can calculate the power dissipation of the device which in this case is 1.5 watts.

$$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{83.3^\circ\text{C/W}} = 1.5 \text{ watts}$$

The 83.3°C/W for the SOT-223 package assumes the recommended collector pad area of 965 sq. mils on a glass epoxy printed circuit board to achieve a power dissipation of 1.5 watts. If space is at a premium, a more realistic approach is to use the device at a  $P_D$  of 833 mW using the footprint shown. Using a board material such as Thermal Clad, a power dissipation of 1.6 watts can be achieved using the same footprint.

MOUNTING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.\*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference should be a maximum of 10°C.

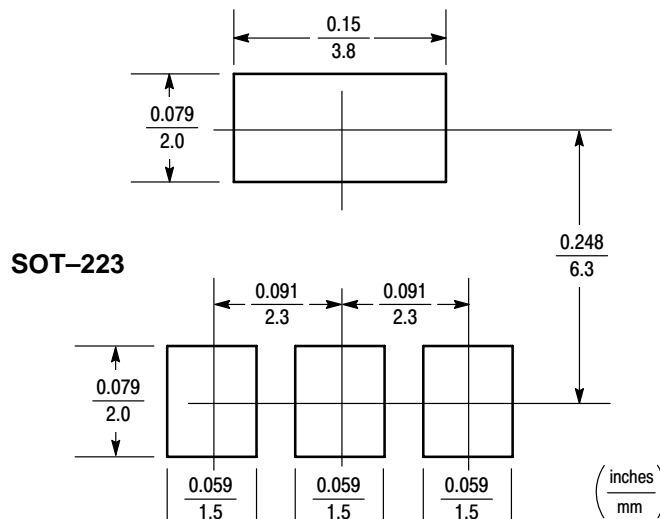
- The soldering temperature and time should not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient should be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling

\* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

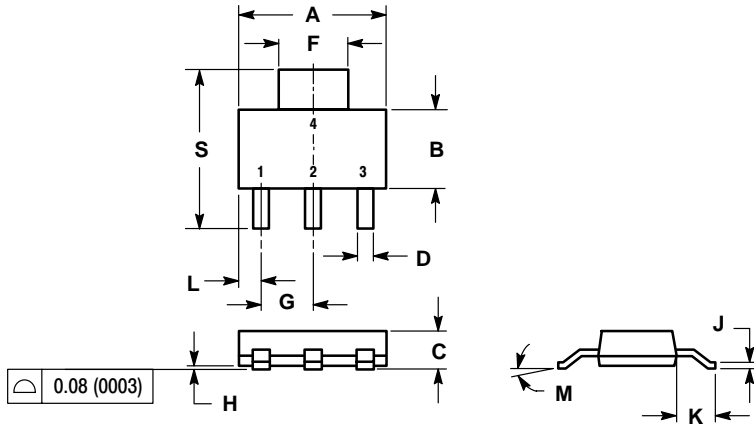
interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



# BCP53T1 Series

## PACKAGE DIMENSIONS

SOT-223  
CASE 318E-04  
ISSUE K



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.

| DIM | INCHES |        | MILLIMETERS |       |
|-----|--------|--------|-------------|-------|
|     | MIN    | MAX    | MIN         | MAX   |
| A   | 0.249  | 0.263  | 6.30        | 6.70  |
| B   | 0.130  | 0.145  | 3.30        | 3.70  |
| C   | 0.060  | 0.068  | 1.50        | 1.75  |
| D   | 0.024  | 0.035  | 0.60        | 0.89  |
| F   | 0.115  | 0.126  | 2.90        | 3.20  |
| G   | 0.087  | 0.094  | 2.20        | 2.40  |
| H   | 0.0008 | 0.0040 | 0.020       | 0.100 |
| J   | 0.009  | 0.014  | 0.24        | 0.35  |
| K   | 0.060  | 0.078  | 1.50        | 2.00  |
| L   | 0.033  | 0.041  | 0.85        | 1.05  |
| M   | 0°     | 10°    | 0°          | 10°   |
| S   | 0.264  | 0.287  | 6.70        | 7.30  |

- STYLE 1:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR

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